

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	10/765,619
		Filing Date	January 27, 2004
		First Named Inventor	Ahn, Kie
		Group Art Unit	2891
		Examiner Name	Sarkar, Asok
Sheet 1 of 3		Attorney Docket No: 1303.033US2	



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EXAMINER

Asok Kumar Sarkar

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Substitute Disclosure Statement Form (PTO-1449)

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		<b>Group Art Unit</b>	2891
		<b>Examiner Name</b>	Sarkar, Asok
Sheet 2 of 3		Attorney Docket No: 1303.033US2	

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EXAMINER As Sh. Kumar Sarkar DATE CONSIDERED 10/4/05

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